Vishay Semiconductors

Standard Recovery Diodes, Generation 2 DO-5 (Stud Version), 50 A



PRODUCT SUMMARY				
I _{F(AV)}	50 A			
Package	DO-203AB (DO-5)			
Circuit configuration	Single diode			

FEATURES

- · High surge current capability
- · Designed for a wide range of applications
- · Stud cathode and stud anode version
- Wire version available
- · Low thermal resistance
- · Designed and qualified for multiple level
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

TYPICAL APPLICATIONS

- Converters
- Power supplies
- · Machine tool controls
- Welding
- · Any high voltage input rectification bridge

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
		50	А			
I _{F(AV)}	T _C	128	°C			
I _{F(RMS)}		78	A			
I _{FSM}	50 Hz	570	٨			
	60 Hz	595	A			
l ² t	50 Hz	1600	A ² s			
1-t	60 Hz	1450	A-5			
V _{RRM}	Range	1400 to 1600	V			
TJ		-55 to 160	°C			

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS						
TYPE NUMBER	VOLTAGE CODE	V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} MAXIMUM AT T _J = 150 °C mA		
	140	1400	1650	4.5		
VS-50PF(R)(W)	160	1600	1900	4.0		

Revision: 07-Apr-14

RoHS COMPLIANT





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FORWARD CONDUCTION						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average forward current		190° conduct	tion, half sine wave		50	А
at case temperature	I _{F(AV)}		lion, nan sine wave		128	°C
Maximum RMS forward current	I _{F(RMS)}				78	А
		t = 10 ms	No voltage		570	A
Maximum peak, one cycle forward,		t = 8.3 ms	reapplied	Sinusoidal half wave, initial T _J = 150 °C	595	
non-repetitive surge current	IFSM	t = 10 ms	100 % V _{RRM}		480	
		t = 8.3 ms	reapplied		500	
		t = 10 ms	No voltage		1600	A ² s
Manufacture 12t for a function	l ² t	t = 8.3 ms	reapplied		1450	
Maximum I ² t for fusing		t = 10 ms	100 % V _{RRM}		1150	
		t = 8.3 ms	reapplied		1050	
Maximum I²√t for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied 16 000 $A^2\sqrt{s}$			A²√s	
Low level value of threshold voltage	V _{F(TO)}	$(16.7 \% x \pi x I_{F(AV)} < I < \pi x I_{F(AV)}), T_J = T_J maximum \qquad 0.77 \qquad V$			V	
Low level value of forward slope resistance	r _f	$(16.7 \% \text{ x } \pi \text{ x } I_{F(AV)} < I < \pi \text{ x } I_{F(AV)}), T_J = T_J \text{ maximum}$ 4.30 m Ω			mΩ	
Maximum forward voltage drop	V _{FM}	$I_{pk} = 125 \text{ A}, T_J = 25 \text{ °C}, t_p = 400 \ \mu \text{s rectangular wave}$ 1.50 V			V	

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-55 to 160	°C	
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	0.51		
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth, flat and greased	0.25	K/W	
Maximum allowable mounting torque (+0 %, -10 %)		Not lubricated thread, tighting on nut ⁽¹⁾	3.4 (30)		
		Lubricated thread, tighting on nut ⁽¹⁾		N·m	
		Not lubricated thread, tighting on hexagon ⁽²⁾	4.2 (37)	(lbf ∙ in)	
		Lubricated thread, tighting on hexagon ⁽²⁾	3.2 (28)		
Approximate weight			15.8	g	
Approximate weight			0.56	OZ.	
Case style		See dimensions - link at the end of datasheet	DO-203AB (DO-5)		

Notes

⁽¹⁾ Recommended for pass-through holes

⁽²⁾ Torque must be appliable only to hexagon and not to plastic structure, recommended for holed heatsink



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CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS			
180°	0.11	0.10					
120°	0.16	0.16					
90°	0.20	0.22	$T_J = T_J maximum$	K/W			
60°	0.29	0.31					
30°	0.49	0.50					

Note

• The table above shows the increment of thermal resistance RthJC when devices operate at different conduction angles than DC

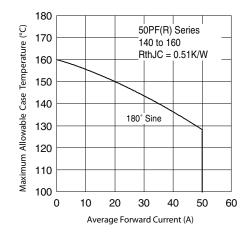


Fig. 1 - Current Ratings Characteristics

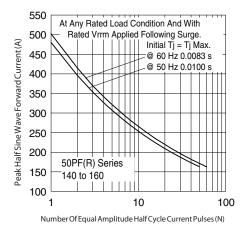


Fig. 2 - Maximum Non-Repetitive Surge Current

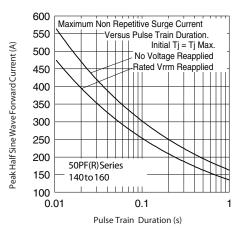


Fig. 3 - Maximum Non-Repetitive Surge Current

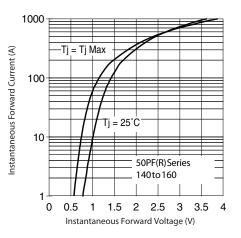


Fig. 4 - Forward Voltage Drop Characteristics

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



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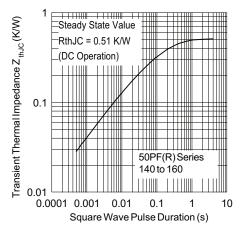


Fig. 5 - Thermal Impedance Z_{thJC} Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	50	PF	R	160	w
	1	2	3	4	5	6
	1 -	Vish	ay Sem	iconduc	tors pro	duct
	2 ·	- 50 = Standard device				
	3 -	3 - PF = Plastic package				
	4	 • None = Stud normal polarity (cathode to stud) 				
		• R	= Stud r	everse	polarity	(anode
	5 -	- Volt	age cod	e x 10 =	= V _{RRM} (see Vol
	6 -	• No	one = St	andard	termina	I
		(s	ee dime	nsions f	or 50PF	(R) I
			= Wire		-	
		(s	ee dime	nsions f	or 50PF	(R)W

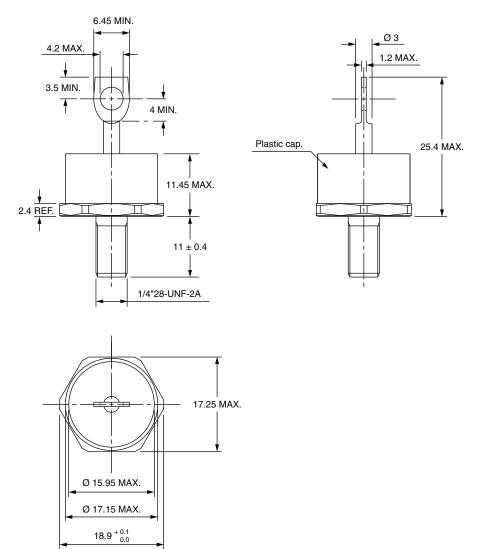
LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?95345		



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DO-203AB (DO-5) for 50PF(R)...(W), 80PF(R)...(W), and 95PF(R)...(W) Series

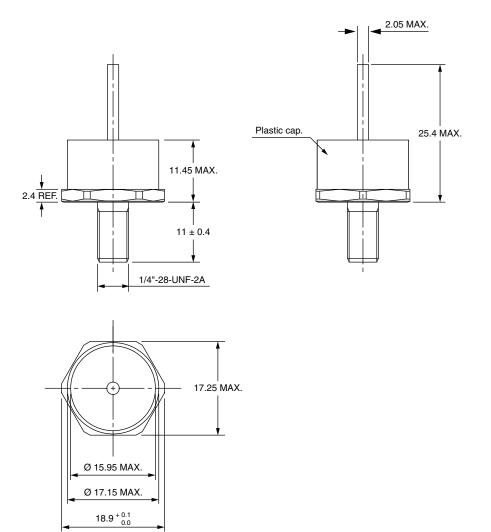
DIMENSIONS FOR 80PF(R), 50PF(R), AND 95PF(R) SERIES in millimeters





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DIMENSIONS FOR 80PF(R)...(W), 50PF(R)...(W), AND 95PF(R)...(W) SERIES in millimeters

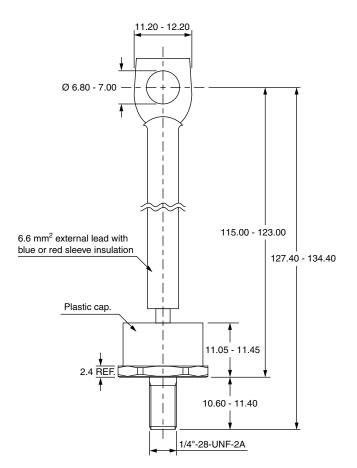


Outline Dimensions



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DIMENSIONS FOR 52PF(R), 82PF(R), AND 97PF(R) SERIES in millimeters





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